

**isc N-Channel MOSFET Transistor**

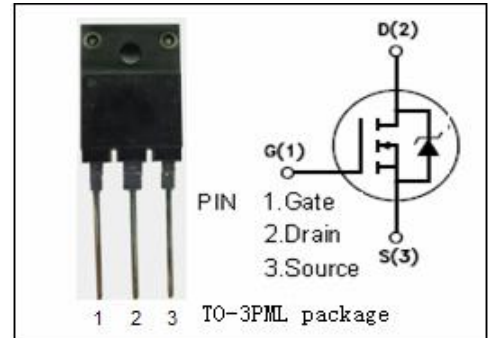
**2SK1224**

**DESCRIPTION**

- Drain Current  $-I_D=4A @ T_C=25^\circ C$
- Drain Source Voltage-  
:  $V_{DSS}=800V(\text{Min})$

**APPLICATIONS**

- Designed for high voltage, high speed power switching

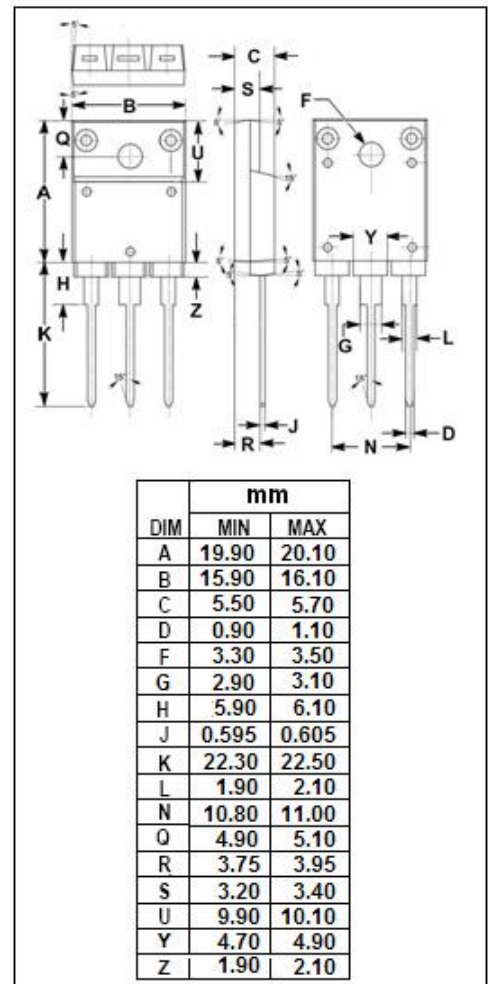


**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage ( $V_{GS}=0$ )	800	V
$V_{GS}$	Gate-Source Voltage	$\pm 30$	V
$I_D$	Drain Current-continuous@ $T_C=25^\circ C$	4	A
$P_{tot}$	Total Dissipation@ $T_C=25^\circ C$	50	W
$T_j$	Max. Operating Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ C$

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.25	$^\circ C/W$
$R_{th\ j-a}$	Thermal Resistance, Junction to Ambient	30	$^\circ C/W$



**isc N-Channel Mosfet Transistor****2SK1224****• ELECTRICAL CHARACTERISTICS (T<sub>C</sub>=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0; I <sub>D</sub> = 1mA	800			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> =1mA	2.5	3.5	5.0	V
R <sub>DS(on)</sub>	Drain-Source On-stage Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> =2A			4.5	Ω
I <sub>GSS</sub>	Gate Source Leakage Current	V <sub>GS</sub> = ±30V; V <sub>DS</sub> = 0			±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =800V; V <sub>GS</sub> = 0			500	uA